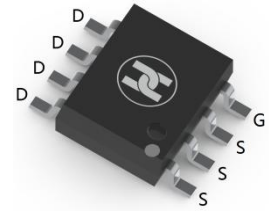
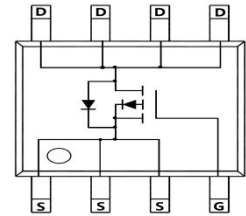


LOW VOLTAGE MOSFET (P-CHANNEL)
FEATURES

- Ultra low on-resistance: $V_{DS}=-30V, I_D=-5.1A, R_{DS(ON)} \leq 85m\Omega @ V_{GS}=-10V$
- Ultra low gate charge
- For load switch or in PWM applications
- Surface Mount device


SOP-8

MECHANICAL DATA

- Case: SOP-8
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.3 grams (approximate)

MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|---|-----------------|------------|--------------|
| Drain-source voltage | V_{DS} | -30 | V |
| Gate-source voltage | V_{GS} | ± 20 | V |
| Continuous drain current | I_D | -5.1 | A |
| Pulsed drain current | I_{DM} | -20 | A |
| Power dissipation | P_D | 2.5 | W |
| Thermal resistance from Junction to ambient | $R_{\theta JA}$ | 50 | $^\circ C/W$ |
| Junction temperature | T_J | 150 | $^\circ C$ |
| Storage temperature | T_{STG} | -55 ~ +150 | $^\circ C$ |

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$ unless otherwise specified)

| Parameter | Symbol | Min | Typ | Max | Unit | Conditions |
|---|----------------|-----|------|-----------|------------|--|
| Off Characteristics | | | | | | |
| Drain-Source breakdown voltage | $V_{(BR)DSS}$ | -30 | | | V | $V_{GS}=0V, I_D=-250\mu A$ |
| Zero gate voltage drain current | I_{DSS} | | | -1 | μA | $V_{DS}=-24V, V_{GS}=0V$ |
| Gate-body leakage current | I_{GSS} | | | ± 100 | nA | $V_{DS}=0V, V_{GS}=\pm 20V$ |
| On Characteristics | | | | | | |
| Gate-threshold voltage | $V_{GS(th)^*}$ | -1 | | -3 | V | $V_{DS}=V_{GS}, I_D=-250\mu A$ |
| Drain-source on-resistance | $R_{DS(ON)^*}$ | | 46 | 53 | m Ω | $V_{GS}=-10V, I_D=-5.1A$ |
| | | | 70 | 85 | m Ω | $V_{GS}=-4.5V, I_D=-4.2A$ |
| Forward transconductance | g_{FS}^* | 4 | 7 | | S | $V_{DS}=-15V, I_D=-4.5A$ |
| Drain-Source Diode Characteristics | | | | | | |
| Diode forward voltage | V_{SD} | | | -1.2 | V | $I_S=-1.7A, V_{GS}=0V$ |
| Dynamic Characteristics | | | | | | |
| Input capacitance | C_{iss} | | 1040 | | pF | $V_{DS}=-15V, V_{GS}=0V, f=1MHz$ |
| Output capacitance | C_{oss} | | 420 | | pF | |
| Reverse transfer capacitance | C_{rss} | | 150 | | pF | |
| Switching Characteristics | | | | | | |
| Total gate charge | Q_g | | 12 | | nC | $V_{GS}=-10V, V_{DS}=-15V, I_D=-5.1A$ |
| Gate-source charge | Q_{gs} | | 2.2 | | nC | |
| Gate-drain charge | Q_{gd} | | 3 | | nC | |
| Turn-on delay time | $t_{d(on)}$ | | 15 | | nS | $V_{GS}=-10V, V_{DD}=-15V, R_{GEN}=6\Omega, I_D=-1A$ |
| Turn-on rise time | t_r | | 13 | | nS | |
| Turn-off delay time | $t_{d(off)}$ | | 58 | | nS | |
| Turn-off fall time | t_f | | 21 | | nS | |

*Pulse test ; Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

LOW VOLTAGE MOSFET (P-CHANNEL)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

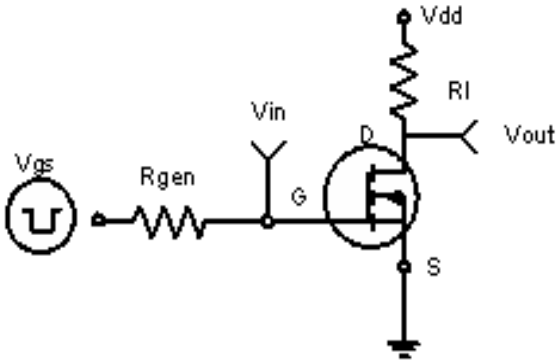


Figure 1: Switching Test Circuit

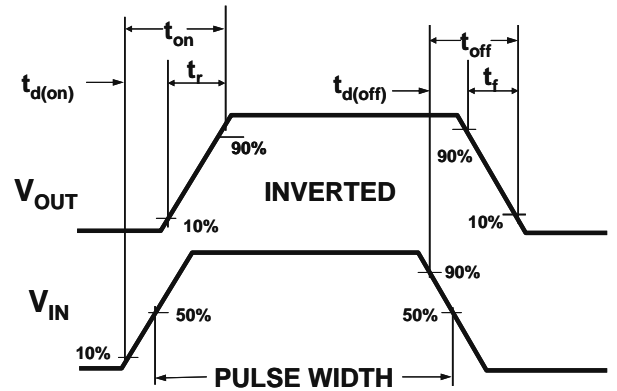


Figure 2: Switching Waveforms

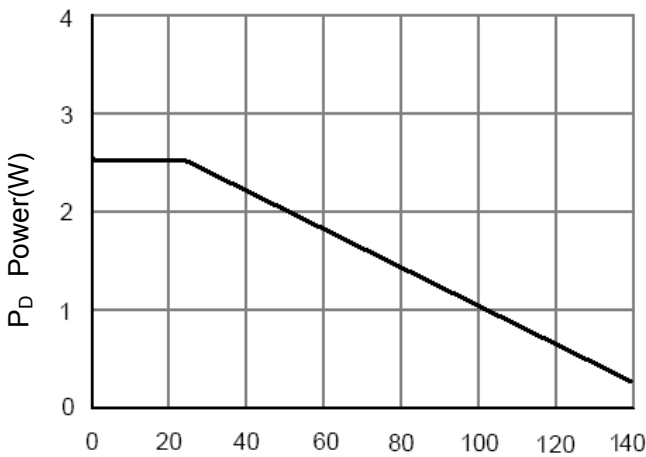


Figure 3 Power Dissipation

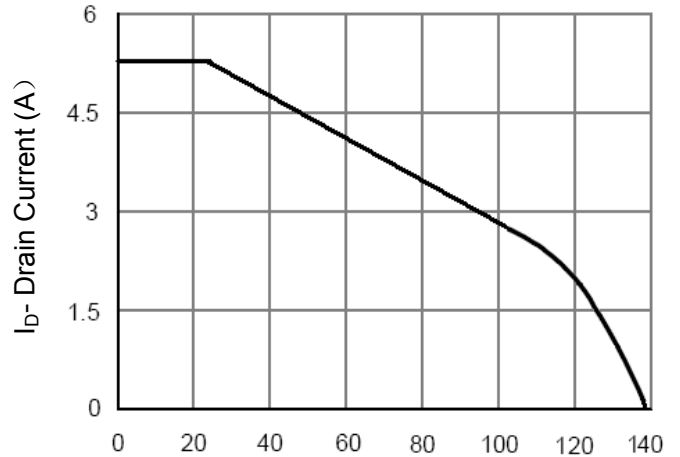


Figure 4 Drain Current

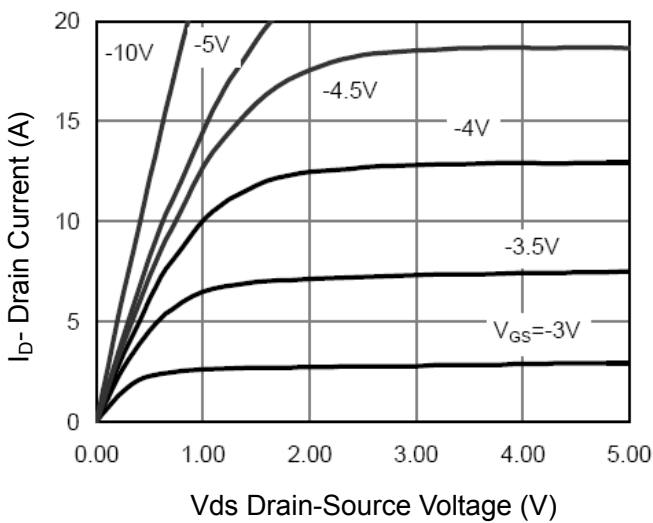


Figure 5 Output CHARACTERISTICS

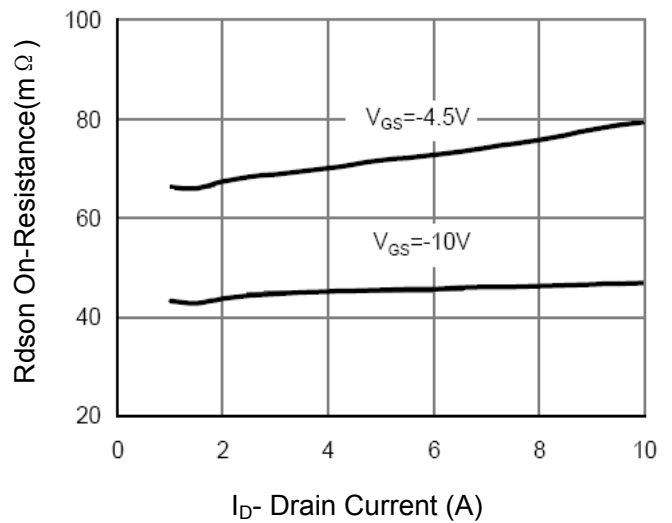


Figure 6 Drain-Source On-Resistance

LOW VOLTAGE MOSFET (P-CHANNEL)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

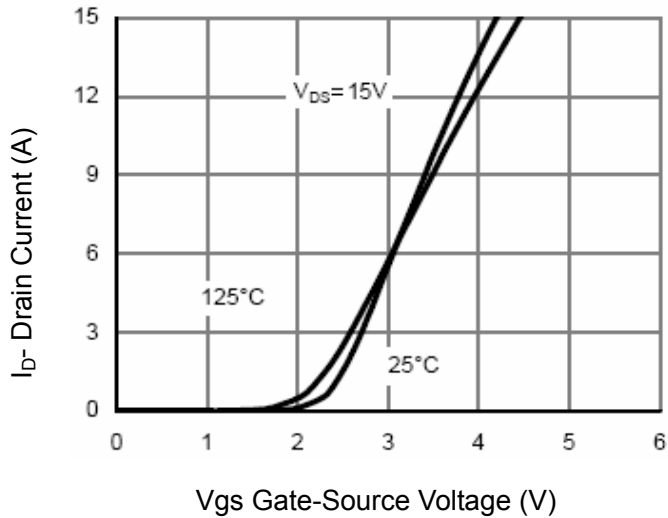


Figure 7 Transfer Characteristics

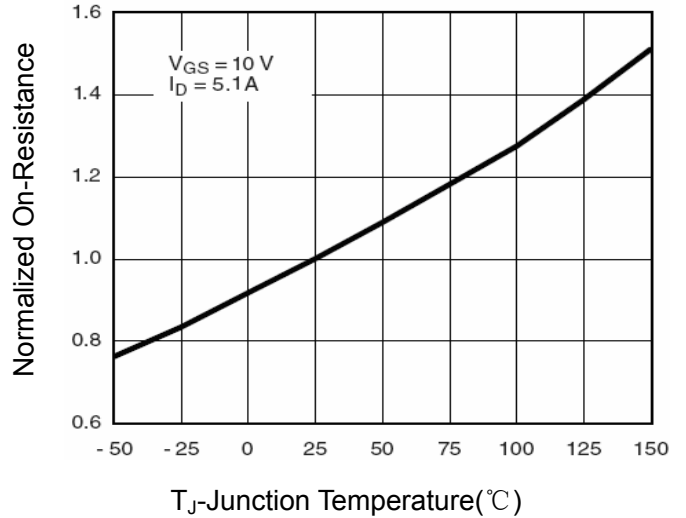


Figure 8 Drain-Source On-Resistance

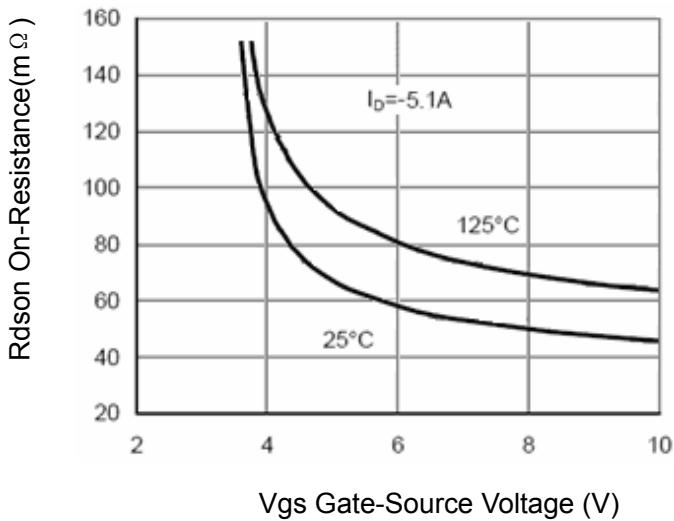


Figure 9 Rdson vs Vgs

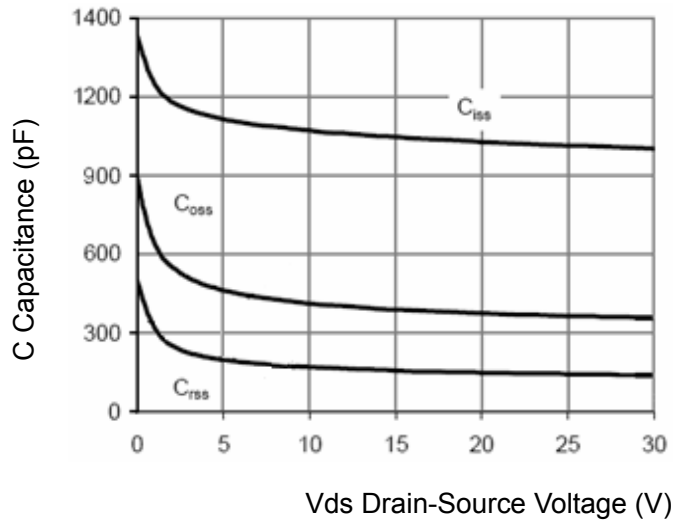


Figure 10 Capacitance vs Vds

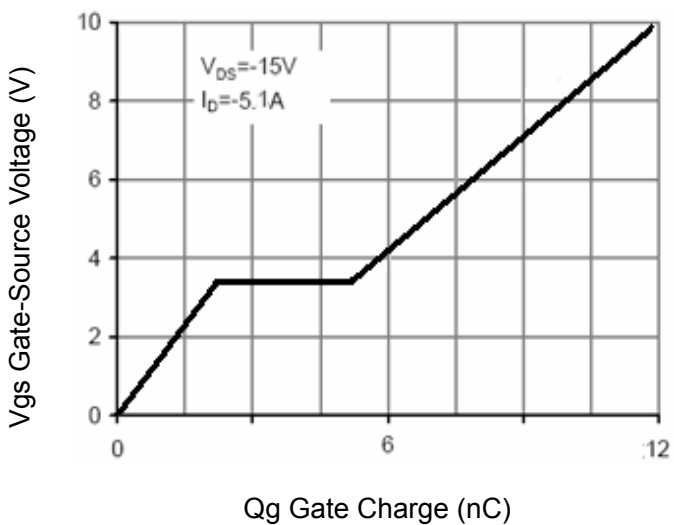


Figure 11 Gate Charge

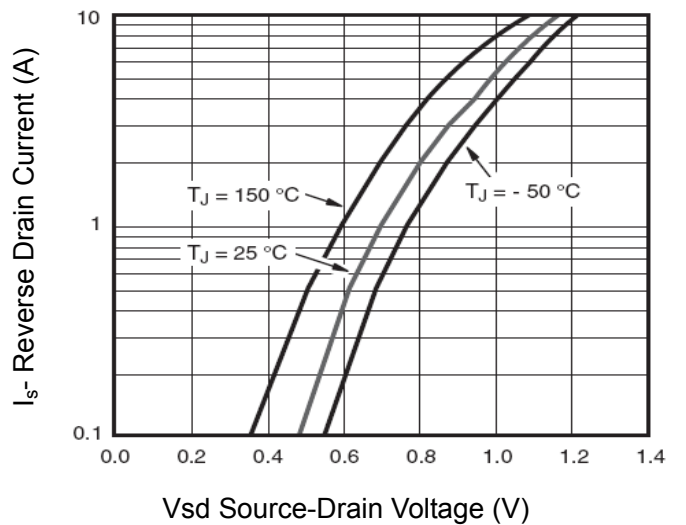


Figure 12 Source- Drain Diode Forward

LOW VOLTAGE MOSFET (P-CHANNEL)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

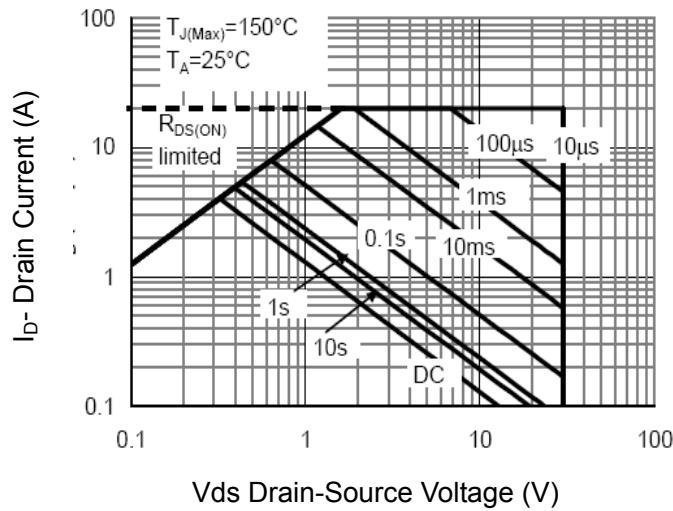


Figure 13 Safe Operation Area

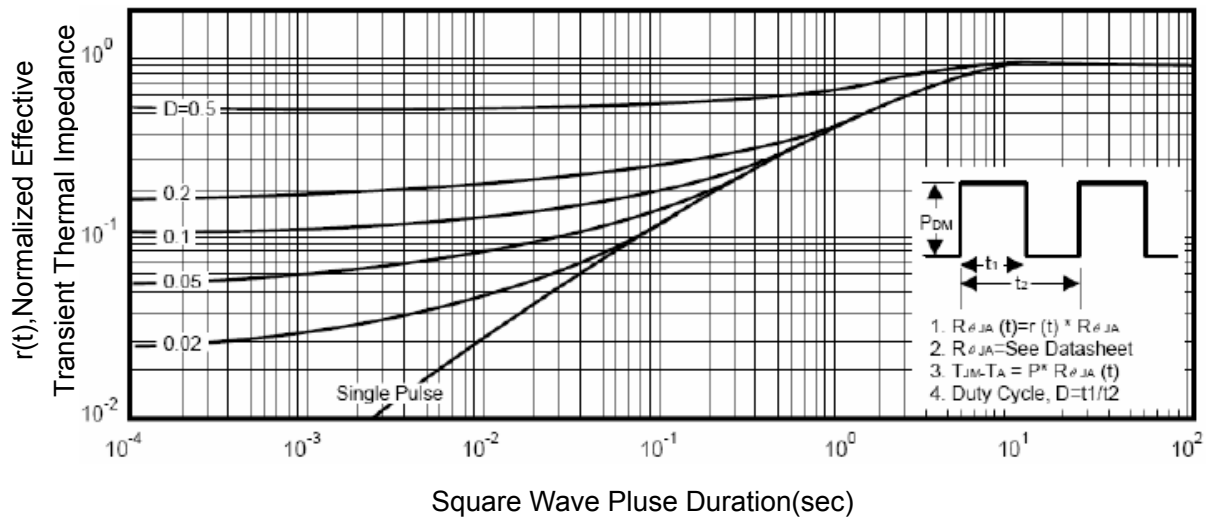
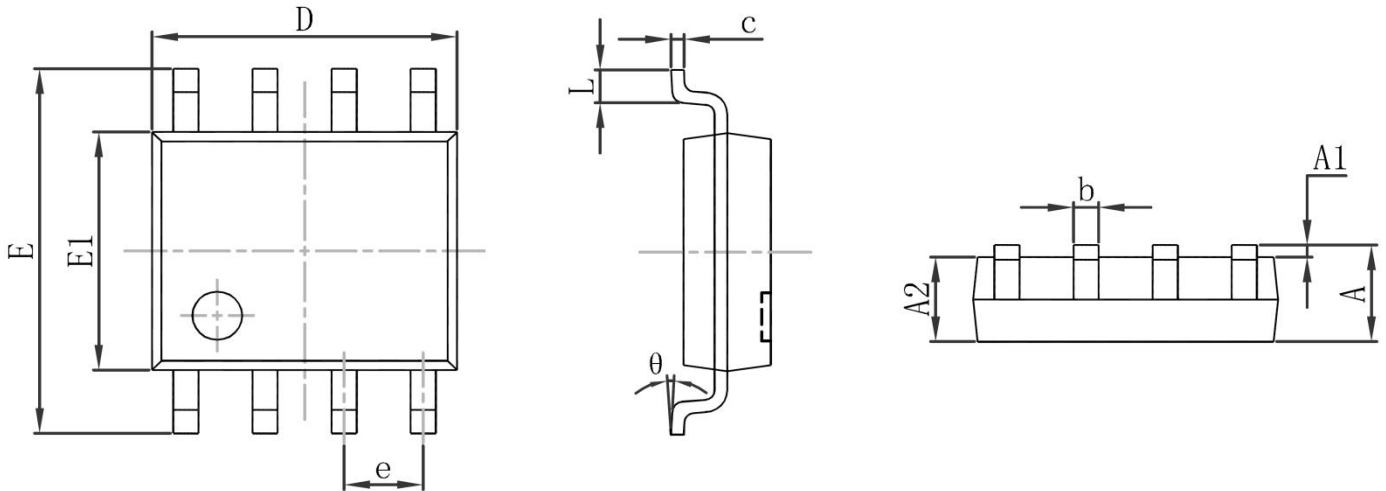
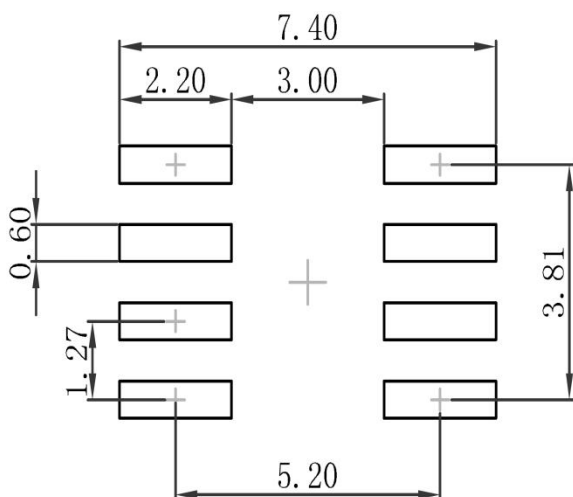


Figure 14 Normalized Maximum Transient Thermal Impedance

LOW VOLTAGE MOSFET (P-CHANNEL)
SOP-8 Package Outline Dimensions


| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|----------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| c | 0.170 | 0.250 | 0.007 | 0.010 |
| D | 4.800 | 5.000 | 0.189 | 0.197 |
| e | 1.270(BSC) | | 0.050 (BSC) | |
| E | 5.800 | 6.200 | 0.228 | 0.244 |
| E1 | 3.800 | 4.000 | 0.150 | 0.157 |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |

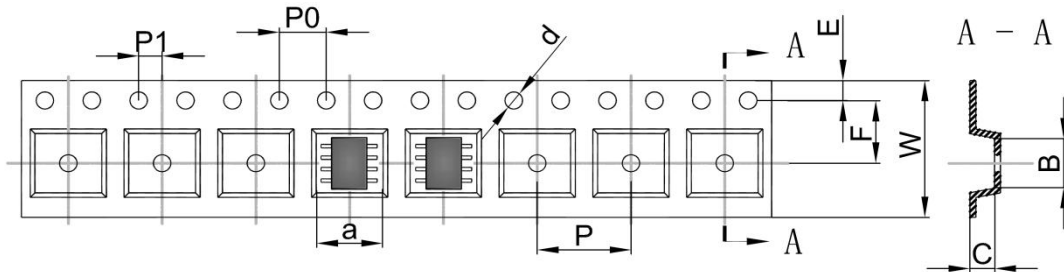
SOP-8 Suggested Pad Layout

Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

LOW VOLTAGE MOSFET (P-CHANNEL)

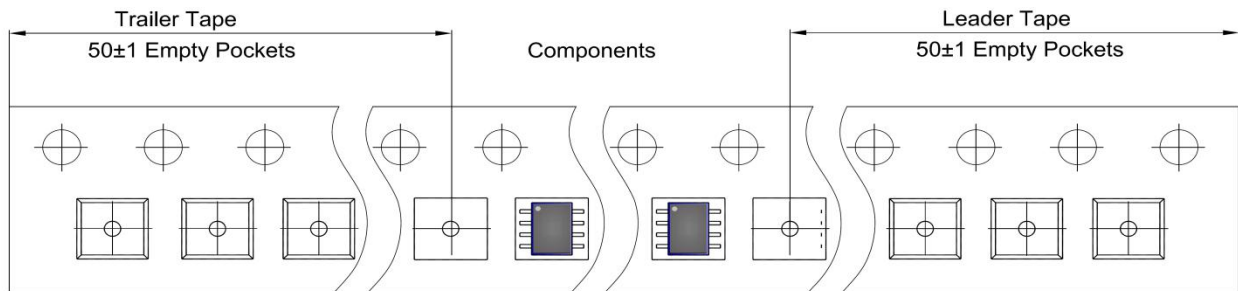
SOP-8 Tape and Reel

SOP-8 Embossed Carrier Tape

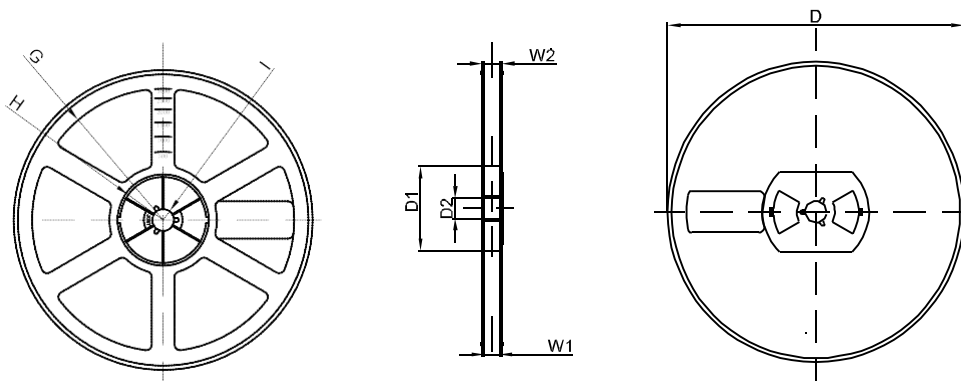


| DIMENSIONS ARE IN MILLIMETER | | | | | | | | | | |
|------------------------------|------|------|------|-------|------|------|------|------|------|-------|
| TYPE | A | B | C | d | E | F | P0 | P | P1 | W |
| SOP-8 | 6.40 | 5.40 | 2.10 | Ø1.50 | 1.75 | 5.50 | 4.00 | 8.00 | 2.00 | 12.00 |
| TOLERANCE | ±0.1 | ±0.1 | ±0.1 | ±0.1 | ±0.1 | ±0.1 | ±0.1 | ±0.1 | ±0.1 | ±0.1 |

SOP-8 Tape Leader and Trailer



SOP-8 Reel



| DIMENSIONS ARE IN MILLIMETER | | | | | | | | |
|------------------------------|---------|--------|-------|---------|--------|-------|-------|-------|
| REEL OPTION | D | D1 | D2 | G | H | I | W1 | W2 |
| 13" DIA | Ø330.00 | 100.00 | 13.00 | R151.00 | R56.00 | R6.50 | 12.40 | 17.60 |
| TOLERANCE | ±2 | ±1 | ±1 | ±1 | ±1 | ±1 | ±1 | ±1 |